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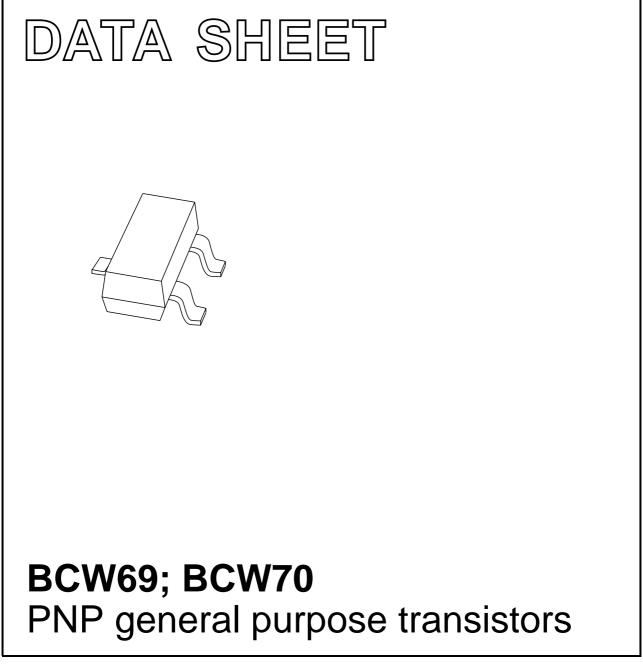
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 19 2004 Feb 06



BCW69; BCW70

PNP general purpose transistors

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package. NPN complements: BCW71 and BCW72.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BCW69	H1*
BCW70	H2*

Note

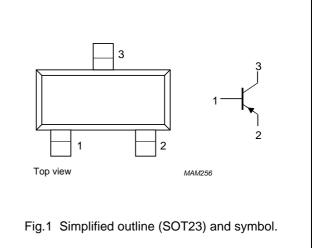
- 1. * = p : Made in Hong Kong.
 - * = t : Made in Malaysia.

* = W : Made in China.

ORDERING INFORMATION

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



TYPE	PACKAGE		
NUMBER	NAME	DESCRIPTION	VERSION
BCW69	_	plastic surface mounted package; 3 leads	SOT23
BCW70			

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	-	-50	V
V _{CEO}	collector-emitter voltage	open base; $I_C = -2 \text{ mA}$	-	-45	V
V _{EBO}	emitter-base voltage	open collector	-	-5	V
I _C	collector current (DC)		-	-100	mA
I _{CM}	peak collector current		-	-200	mA
I _{BM}	peak base current		-	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	-	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector cut-off current	$I_{E} = 0; V_{CB} = -20 V$	-	_	-100	nA
		$I_E = 0; V_{CB} = -20 V; T_j = 100 \ ^{\circ}C$	-	-	-10	μA
I _{EBO}	emitter cut-off current	$I_{C} = 0; V_{EB} = -5 V$	-	-	-100	nA
h _{FE}	DC current gain	$I_{C} = -10 \ \mu A; V_{CE} = -5 \ V$				
	BCW69		-	90	-	
	BCW70		_	150	_	
	DC current gain	$I_{C} = -2 \text{ mA}; V_{CE} = -5 \text{ V}$				
	BCW69		120	_	260	
	BCW70		215	_	500	
V _{CEsat}	collector-emitter saturation	$I_{\rm C} = -10 \text{ mA}; I_{\rm B} = -0.5 \text{ mA}$	_	-80	-300	mV
	voltage	$I_{C} = -50 \text{ mA}; I_{B} = -2.5 \text{ mA}; \text{ note } 1$	_	-150	_	mV
V _{BEsat}	base-emitter saturation voltage	$I_{\rm C} = -10$ mA; $I_{\rm B} = -0.5$ mA	_	-720	_	mV
		$I_{C} = -50 \text{ mA}; I_{B} = -2.5 \text{ mA}; \text{ note } 1$	_	-810	_	mV
V _{BE}	base-emitter voltage	$I_{C} = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	_	-750	mV
C _c	collector capacitance	$I_E = I_e = 0; V_{CB} = -10 \text{ V};$ f = 1 MHz	-	4.5	-	pF
f _T	transition frequency	$I_{C} = -10 \text{ mA}; V_{CE} = -5 \text{ V};$ f = 100 MHz	100	-	-	MHz
F	noise figure	$ I_{C} = -200 \ \mu\text{A}; \ V_{CE} = -5 \ \text{V}; \\ R_{S} = 2 \ \text{k}\Omega; \ \text{f} = 1 \ \text{kHz}; \ \text{B} = 200 \ \text{Hz} $	-	-	10	dB

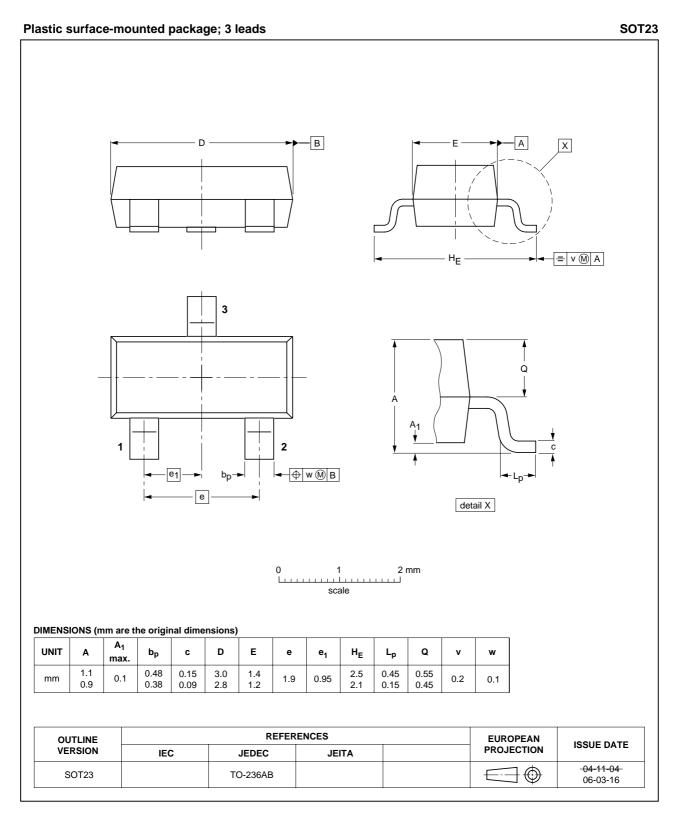
Note

1. Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

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BCW69; BCW70

PACKAGE OUTLINE



PNP general purpose transistors

BCW69; BCW70

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
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NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

Contact information

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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